

## High Efficiency Standard Rectifier

$$V_{RRM} = 800 \text{ V}$$

$$I_{FAV} = 10 \text{ A}$$

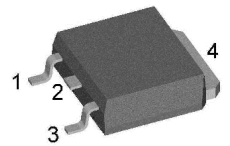
$$V_F = 1.16 \text{ V}$$

### Single Diode

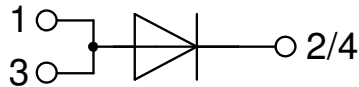
#### Part number

**DLA10IM800UC**

Marking on Product: MARLUI



Backside: cathode



#### Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very low forward voltage drop
- Improved thermal behaviour

#### Applications:

- Diode for main rectification
- For single and three phase bridge configurations

#### Package: TO-252 (DPak)

- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0

#### Terms Conditions of usage:

The data contained in this product data sheet is exclusively intended for technically trained staff. The user will have to evaluate the suitability of the product for the intended application and the completeness of the product data with respect to his application. The specifications of our components may not be considered as an assurance of component characteristics. The information in the valid application- and assembly notes must be considered. Should you require product information in excess of the data given in this product data sheet or which concerns the specific application of your product, please contact the sales office, which is responsible for you.

Due to technical requirements our product may contain dangerous substances. For information on the types in question please contact the sales office, which is responsible for you.

Should you intend to use the product in aviation, in health or live endangering or life support applications, please notify. For any such application we urgently recommend

- to perform joint risk and quality assessments;

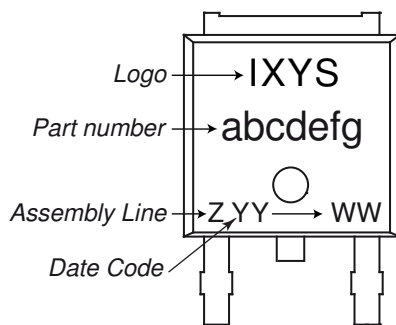
- the conclusion of quality agreements;

- to establish joint measures of an ongoing product survey, and that we may make delivery dependent on the realization of any such measures.

Rectifier				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
$V_{RSM}$	max. non-repetitive reverse blocking voltage					900	V
$V_{RRM}$	max. repetitive reverse blocking voltage					800	V
$I_R$	reverse current	$V_R = 800$ V	$T_{VJ} = 25^\circ\text{C}$			5	$\mu\text{A}$
		$V_R = 800$ V	$T_{VJ} = 150^\circ\text{C}$			0.05	mA
$V_F$	forward voltage drop	$I_F = 10$ A	$T_{VJ} = 25^\circ\text{C}$			1.22	V
		$I_F = 20$ A				1.40	V
		$I_F = 10$ A	$T_{VJ} = 150^\circ\text{C}$			1.16	V
		$I_F = 20$ A				1.45	V
$I_{FAV}$	average forward current	$T_C = 145^\circ\text{C}$ rectangular	$T_{VJ} = 175^\circ\text{C}$ d = 0.5			10	A
$V_{FO}$	threshold voltage	} for power loss calculation only				0.84	V
$r_F$	slope resistance					30	m $\Omega$
$R_{thJC}$	thermal resistance junction to case					2	K/W
$R_{thCH}$	thermal resistance case to heatsink				0.50		K/W
$P_{tot}$	total power dissipation			$T_C = 25^\circ\text{C}$		75	W
$I_{FSM}$	max. forward surge current	t = 10 ms; (50 Hz), sine	$T_{VJ} = 45^\circ\text{C}$			120	A
		t = 8,3 ms; (60 Hz), sine	$V_R = 0$ V			130	A
		t = 10 ms; (50 Hz), sine	$T_{VJ} = 150^\circ\text{C}$			100	A
		t = 8,3 ms; (60 Hz), sine	$V_R = 0$ V			110	A
$I^2t$	value for fusing	t = 10 ms; (50 Hz), sine	$T_{VJ} = 45^\circ\text{C}$			72	A <sup>2</sup> s
		t = 8,3 ms; (60 Hz), sine	$V_R = 0$ V			70	A <sup>2</sup> s
		t = 10 ms; (50 Hz), sine	$T_{VJ} = 150^\circ\text{C}$			50	A <sup>2</sup> s
		t = 8,3 ms; (60 Hz), sine	$V_R = 0$ V			50	A <sup>2</sup> s
$C_J$	junction capacitance	$V_R = 400$ V; f = 1 MHz		$T_{VJ} = 25^\circ\text{C}$		3	pF

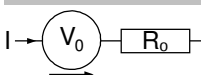
Package TO-252 (DPak)			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
$I_{RMS}$	RMS current	per terminal <sup>1)</sup>			20	A
$T_{VJ}$	virtual junction temperature		-55		175	°C
$T_{op}$	operation temperature		-55		150	°C
$T_{stg}$	storage temperature		-55		150	°C
<b>Weight</b>				0.3		g
$F_C$	mounting force with clip		20		60	N

<sup>1)</sup>  $I_{RMS}$  is typically limited by the pin-to-chip resistance (1); or by the current capability of the chip (2). In case of (1) and a product with multiple pins for one chip-potential, the current capability can be increased by connecting the pins as one contact.

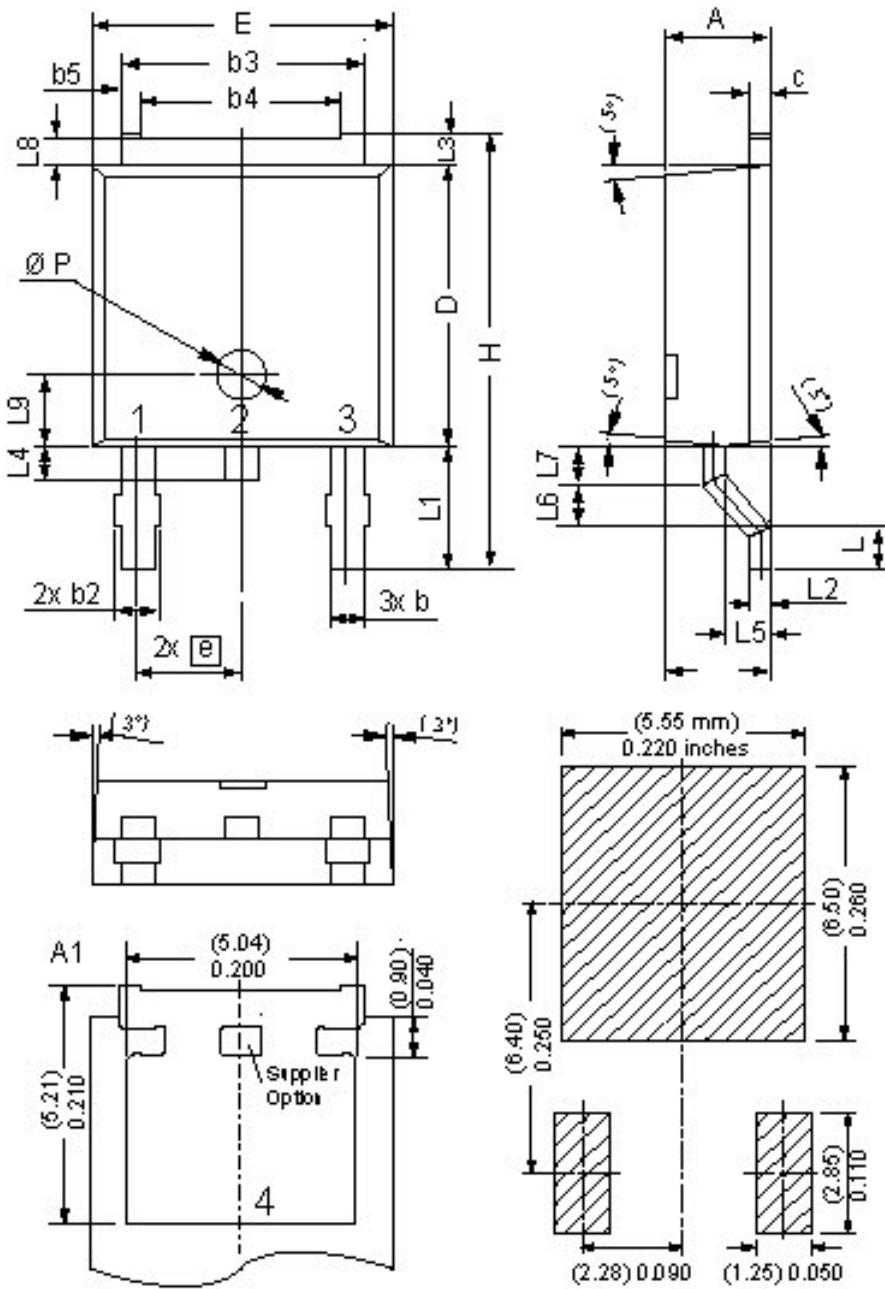
**Product Marking**

**Part description**

- D = Diode
- L = High Efficiency Standard Rectifier
- A = (up to 1200V)
- 10 = Current Rating [A]
- IM = Single Diode
- 800 = Reverse Voltage [V]
- UC = TO-252AA (DPak)

Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DLA10IM800UC	MARLUI	Tape & Reel	2500	503668

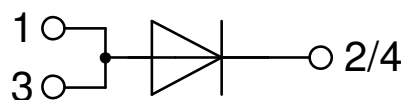
**Equivalent Circuits for Simulation**
*\* on die level*
 $T_{VJ} = 175\text{ °C}$ 

**Rectifier**

$V_{0\ max}$	threshold voltage	0.84	V
$R_{0\ max}$	slope resistance *	27	mΩ

**Outlines TO-252 (DPak)**


Dim	Millimeters		Inches	
	min	max	min	max
A	2.20	2.40	0.087	0.094
A1	2.10	2.50	0.083	0.098
b	0.66	0.86	0.026	0.034
b2	-	0.96	-	0.038
b3	5.04	5.64	0.198	0.222
b4	4.34	BSC	0.171	BSC
b5	0.50	BSC	0.020	BSC
c	0.40	0.86	0.016	0.034
D	5.90	6.30	0.232	0.248
E	6.40	6.80	0.252	0.268
e	2.10	2.50	0.083	0.098
H	9.20	10.10	0.362	0.398
L	0.55	1.28	0.022	0.050
L1	2.50	2.90	0.098	0.114
L2	0.40	0.60	0.016	0.024
L3	0.50	0.90	0.020	0.035
L4	0.60	1.00	0.024	0.039
L5	0.82	1.22	0.032	0.048
L6	0.79	0.99	0.031	0.039
L7	0.81	1.01	0.032	0.040
L8	0.40	0.80	0.016	0.031
L9	1.50	BSC	0.059	BSC
Ø P	1.00	BSC	0.039	BSC

Recommended  
min. foot print



## Rectifier

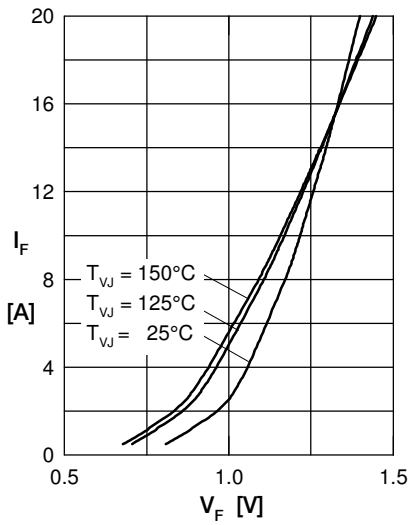


Fig. 1 Forward current versus voltage drop

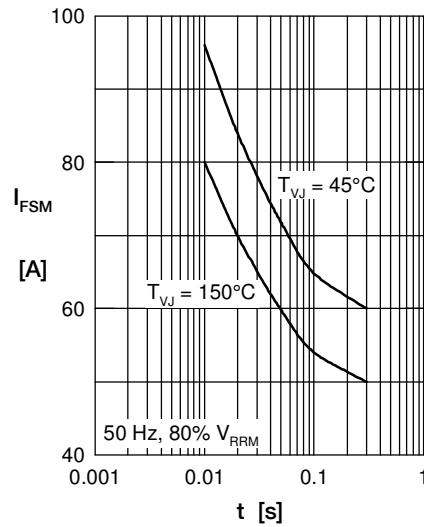


Fig. 2 Surge overload current

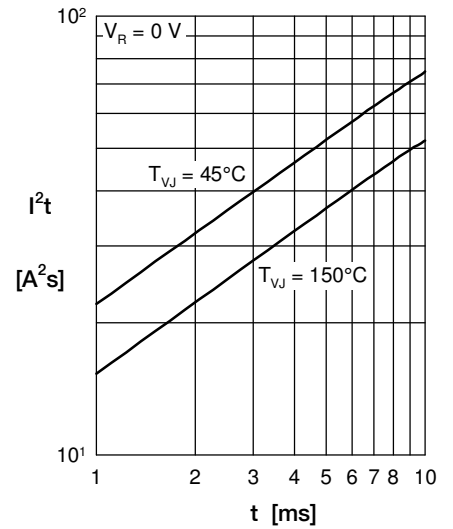


Fig. 3  $I^2t$  versus time

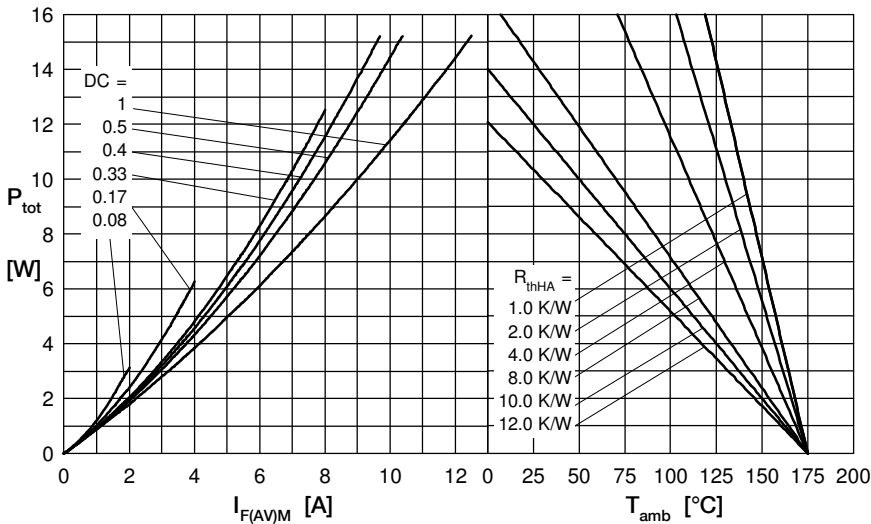


Fig. 4 Power dissipation versus direct output current and ambient temperature

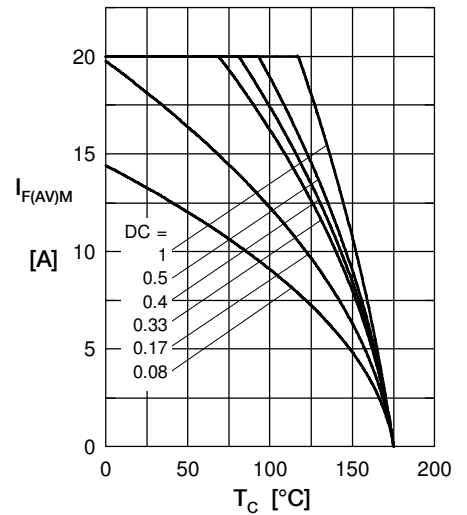


Fig. 5 Max. forward current vs. case temperature

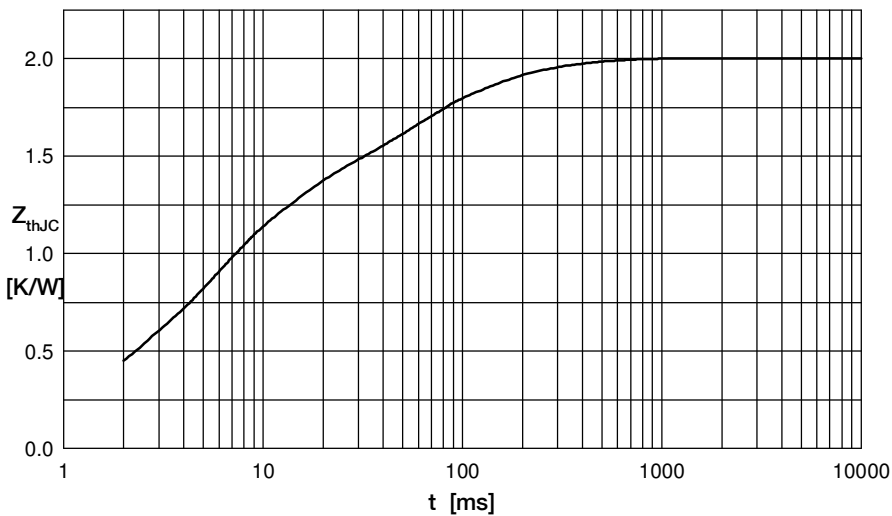


Fig. 6 Transient thermal impedance junction to case

Constants for  $Z_{thJC}$  calculation:

i	$R_{thi}$ (K/W)	$t_i$ (s)
1	1.1	0.005
2	0.06	0.0003
3	0.14	0.045
4	0.2	0.2
5	0.5	0.05